

## IR Laser Diode

### Application

Industrial use / Biomedical

### Property

Wavelength  $\lambda = 980\text{nm}$

Output Power = 50mW

Package Type =  $\varphi 5.6\text{mm}$

### Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer.

Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.

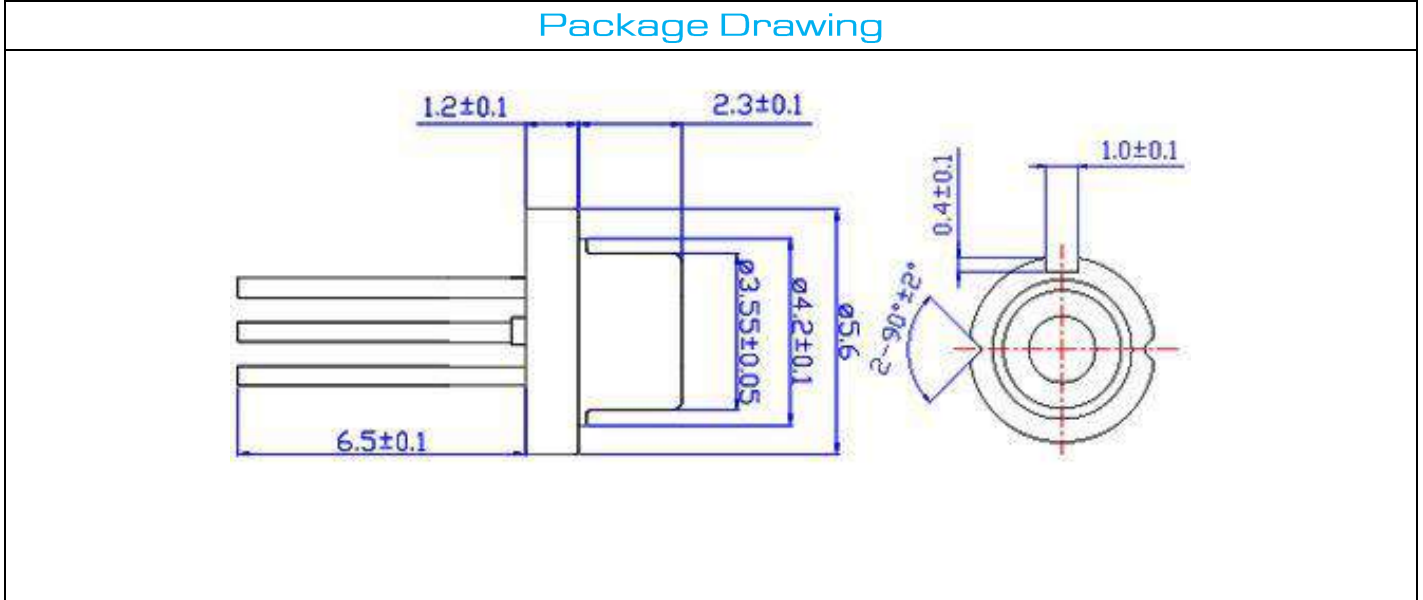
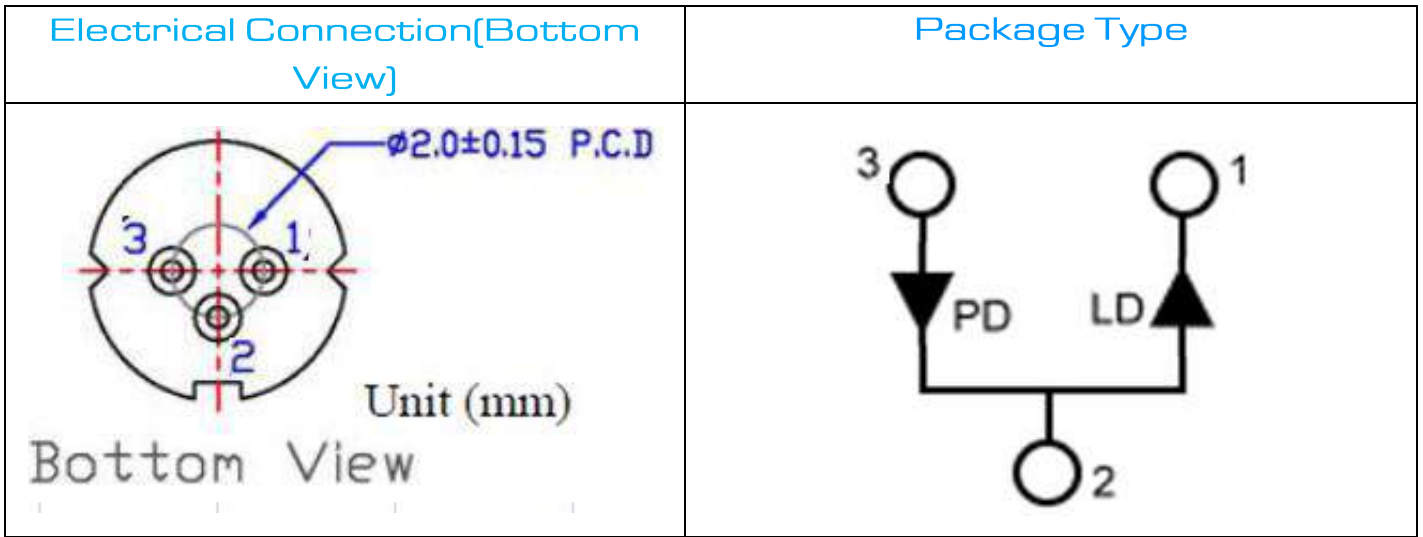


### IR Laser Diode Key features

Absolute Maximum Rating at Tc=25°C			
Items	Symbols	Values	Unit
Optical Output Power	Po(CW)	50	mW
Reverse Voltage	V	2	V
Operating Temperature	To	-10~+40	°C
Storage Temperature	Ts	-10~+70	°C

Electrical and Optical Characteristics at Tc=25°C						
Item	Symbols	Min	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	-	50	mW	-
Threshold Current	Ith	-	12	20	mA	-
Operating Current	Iop	-	75	100	mA	Po=50mW
Operating Voltage	Vop	1	1.5	2.1	V	Po=50mW
Peak Wavelength	$\lambda_p$	970	980	990	nm	Po=50mW

Beam Divergence	$\theta_{//}$	8	13	18	deg	Po=50mW
	$\theta_{\perp}$	25	30	35	deg	Po=50mW



Specifications are subject to change without notice.

